

Supporting Information

Optimization of the Crystalline Nanostructure and Morphology of Tri-IF-dione for High-performance Stable N-type Field-Effect Transistors

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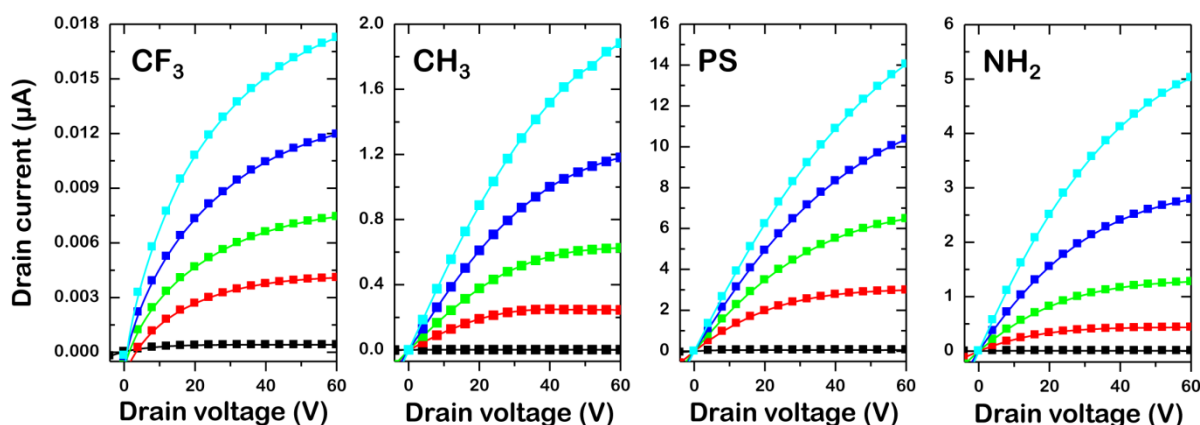


Figure S1. Output characteristics (I_D vs. V_D) of TriF-IF-dione FETs fabricated on the NH_2 -, PS-, CH_3 -, and CF_3 -treated SiO_2 substrates.